## AM40P02-20D

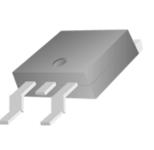
## **Analog Power**

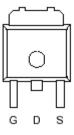
## P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low r<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature TO-252 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range (±25) for battery pack applications

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	I <sub>D</sub> (A)		
-20	$20 @ V_{GS} = -4.5V$	41		
-20	$35 @ V_{GS} = -2.5V$	31		





TO-252

Top View

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)				
Parameter			Maximum	Units
Drain-Source Voltage		V <sub>DS</sub>	-20	V
Gate-Source Voltage		V <sub>GS</sub>	±12	v
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I <sub>D</sub>	41	А
Pulsed Drain Current <sup>b</sup>			±40	A
Continuous Source Current (Diode Conduction) <sup>a</sup>			-30	Α
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$	P <sub>D</sub>	50	W
Operating Junction and Storage Temperature Range			-55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	50	°C/W	
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	°C/W	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Parameter	Symptical		Limits			TT	
Farameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	VGS(th)	$V_{DS} = V_{GS}, I_D = -250 \text{ uA}$	-0.7				
Gate-Body Leakage	Igss	$V_{DS} = 0 V, V_{GS} = \pm 25 V$			±100	nA	
Zara Cata Valtaga Drain Currant	IDSS	$V_{DS} = -16 V, V_{GS} = 0 V$			-1	uA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-5	uA	
On-State Drain Current <sup>A</sup>	ID(on)	$V_{DS} = -5 V$ , $V_{GS} = -4.5 V$	-41			Α	
	IDS(on)	$V_{GS} = -4.5 \text{ V}, \text{ ID} = -20.5 \text{ A}$			20	mΩ	
Drain-Source On-Resistance <sup>A</sup>		$V_{GS} = -2.5 \text{ V}, I_D = -15.5 \text{ A}$			35		
Forward Tranconductance <sup>A</sup>	gś	$V_{DS} = -10 \text{ V}, \text{ I}_D = -20.5 \text{ A}$		31		S	
Diode Forward Voltage	Vsd	$I_{S} = -41 \text{ A}, V_{GS} = 0 \text{ V}$		-0.7		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	$V_{DS} = -10 V$ , $V_{GS} = -4.5 V$ ,		30			
Gate-Source Charge	Qgs	$V_{DS} = -10 \text{ v}, \text{ V}_{GS} = -4.5 \text{ v},$ $I_{D} = -21 \text{ A}$		4		nC	
Gate-Drain Charge	Qgd	ID = -21 A		6			
Switching							
Turn-On Delay Time	t <sub>d(on)</sub>			15		JĪ	
Rise Time	tr	$V_{DD}$ = -10 V, $R_L$ = 15 $\Omega$ , ID = -41 A,		12		nS	
Turn-Off Delay Time	td(off)	$VGEN = -10 V, RG = 6\Omega$		62			
Fall-Time	tf	7		46			

Notes

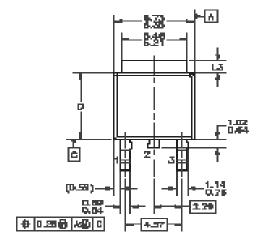
(C)

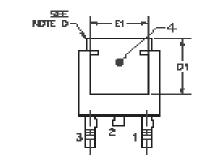
- a. Pulse test:  $PW \le 300$  us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

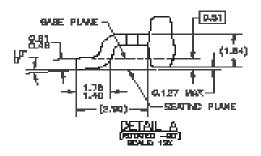
Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

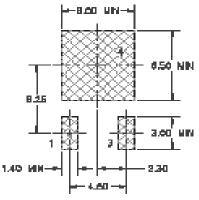
Publication Order Number: DS-AM40P02-20\_C

## Package Information

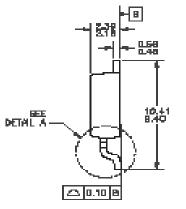








LAND PATTERN RECOMMENDATION



- NOTES: UNLESS OTHERWISE SPECIFIED
  - 삵
- ALL CHERNERARE IN MULIMETERS. THIS PACKAGE CONFORME TO JETEC, TO-262, ISSNE C, VARIATION AA IN AB, DATED NOW 1989. Dimensioning and toleranging per
  - C)
  - ABNE 114-00-1004. HEAT SINK TOP EDGE COULD BE IN CHANFERED CORNERS OR EDGE PROTRASION. DIMENSIONS L3,0,61-001 TABLE: D) E)
    - OFTIGE M. GETTER AS

14 (Jan 19 19 19 19 19 19 19 19 19 19 19 19 19	
4.422	
	447 88